

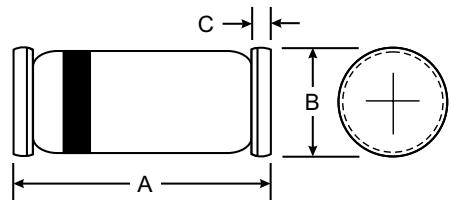


Features

- Silicon Epitaxial Planner Diode
- Low Reverse Current and Low Forward Voltage
- Low Current Rectification and High Speed Switching
- High Reliability

Mechanical Data

- Case: SOD-80/LL34, Glass
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.05 grams (approx.)



LL34/ SOD-80		
Dim	Min	Max
A	3.30	3.70
B	1.30	1.60
C	0.28	0.50

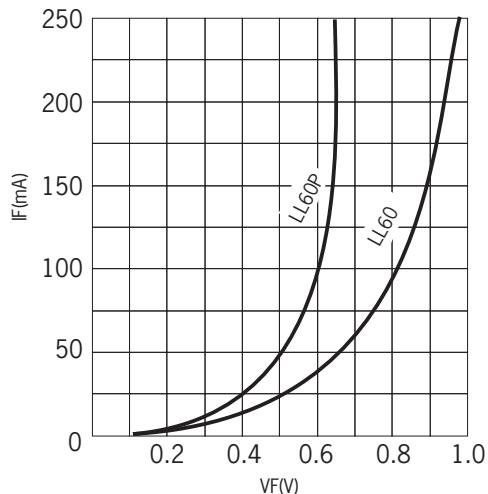
All Dimensions in mm

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

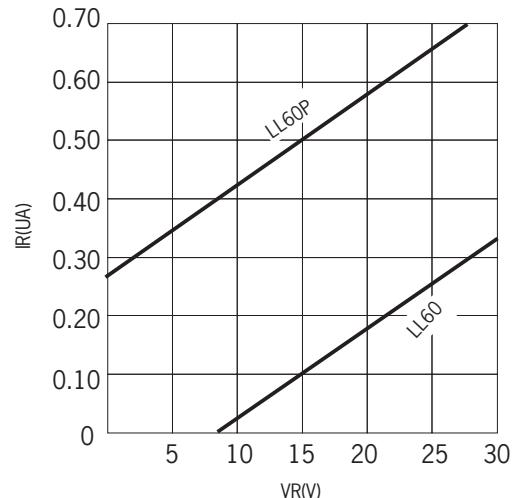
Characteristic	Symbol	LL60	LL60P	Unit
Pepetitive Peak Reverse Voltage	V_{RRM}	40	45	V
Non-Repetitive Peak Forward Surge Current @ $t=1\text{s}$	I_{FSM}	150	500	mA
Forward Continuous Current, $T_A = 25^\circ\text{C}$	I_F	30	50	mA
Operating and Strorage Temperature Range	T_J, T_{STG}	-65 to +125		°C

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

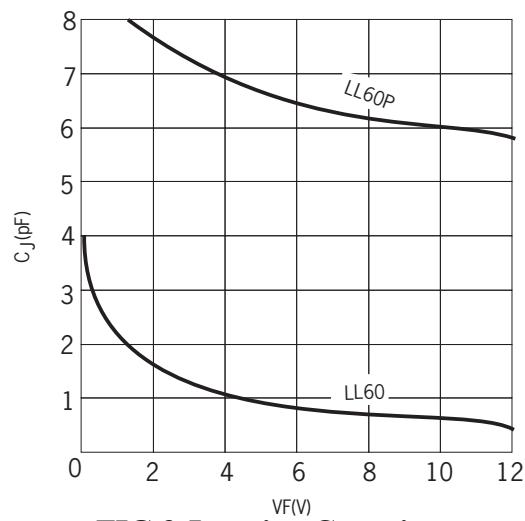
Characteristic	Symbol	Min	Tpy	Max	Unit
Forward Voltage $I_F=1\text{ mA}$ LL60	V_F	-	0.32	0.5	V
		-	0.24	0.5	
LL60P		-	0.65	1.0	
$I_F=30\text{ mA}$ LL60		-	0.65	1.0	
$I_F=200\text{ mA}$ LL60P		-	0.65	1.0	
Reverse Current $V_R=15\text{ V}$ LL60	I_R	-	0.1	0.5	uA
LL60P		-	0.5	1.0	
$V_R=10\text{ V}, f=1\text{ MHz}$ LL60P		-	2.0	-	PF
$V_R=1\text{ V}, f=1\text{ MHz}$ LL60		-	6.0	-	
Reverse Recovery Time $I_F=I_R=1\text{ mA}, I_{rr}=1\text{ mA}, R_c=100\Omega$	T_{rr}	-	-	1.0	nS



**FIG.1 Foward Current vs.
Forward Voltage**



**FIG.2 Reverse Current vs.
Continuous Reverse Votlage**



**FIG.3 Junction Capacitance vs.
Continuous Reverse Applied Voltage**